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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	87
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 17x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302vbt6tr

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F302xB/STM32F302xC microcontrollers.

This STM32F302xB/STM32F302xC datasheet should be read in conjunction with the STM32F302xx reference manual (RM0365). The reference manual is available from the STMicroelectronics website www.st.com.

For information on the Cortex[®]-M4 core with FPU, please refer to:

- **Cortex[®]-M4 with FPU Technical Reference Manual**, available from ARM website www.arm.com.
- **STM32F3xxx and STM32F4xxx Cortex[®]-M4 programming manual (PM0214)** available from our website www.st.com.



3.10 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current capable except for analog inputs.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allows I/O toggling up to 36 MHz.

3.11 Direct memory access (DMA)

The flexible general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each of the 12 DMA channels is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose timers, DAC and ADC.

3.12 Interrupts and events

3.12.1 Nested vectored interrupt controller (NVIC)

The STM32F302xB/STM32F302xC devices embed a nested vectored interrupt controller (NVIC) able to handle up to 66 maskable interrupt channels and 16 priority levels.

The NVIC benefits are the following:

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

The NVIC hardware block provides flexible interrupt management features with minimal interrupt latency.

- 17-bit Auto-reload counter for periodic interrupt with wakeup from STOP/STANDBY capability.

The RTC clock sources can be:

- A 32.768 kHz external crystal
- A resonator or oscillator
- The internal low-power RC oscillator (typical frequency of 40 kHz)
- The high-speed external clock divided by 32.

3.19 Inter-integrated circuit interface (I²C)

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard (up to 100 KHz), fast (up to 400 KHz) and fast mode + (up to 1 MHz) modes.

Both support 7-bit and 10-bit addressing modes, multiple 7-bit slave addresses (2 addresses, 1 with configurable mask). They also include programmable analog and digital noise filters.

Table 6. Comparison of I2C analog and digital filters

	Analog filter	Digital filter
Pulse width of suppressed spikes	50 ns	Programmable length from 1 to 15 I2C peripheral clocks
Benefits	Available in Stop mode	1. Extra filtering capability vs. standard requirements. 2. Stable length
Drawbacks	Variations depending on temperature, voltage, process	Wakeup from Stop on address match is not available when digital filter is enabled.

In addition, they provide hardware support for SMBUS 2.0 and PMBUS 1.1: ARP capability, Host notify protocol, hardware CRC (PEC) generation/verification, timeouts verifications and ALERT protocol management. They also have a clock domain independent from the CPU clock, allowing the I2Cx (x=1,2) to wake up the MCU from Stop mode on address match.

The I2C interfaces can be served by the DMA controller.

Refer to [Table 7](#) for the features available in I2C1 and I2C2.

Table 7. STM32F302xB/STM32F302xC I²C implementation

I2C features ⁽¹⁾	I2C1	I2C2
7-bit addressing mode	X	X
10-bit addressing mode	X	X
Standard mode (up to 100 kbit/s)	X	X
Fast mode (up to 400 kbit/s)	X	X
Fast Mode Plus with 20mA output drive I/Os (up to 1 Mbit/s)	X	X
Independent clock	X	X

Table 13. STM32F302xB/STM32F302xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
J9	24	15	11	PA1	I/O	TTa	(4)	USART2_RTS_DE, TIM2_CH2, TSC_G1_IO2, TIM15_CH1N, RTC_REFIN, EVENTOUT	ADC1_IN2, COMP1_INP, OPAMP1_VINP
F7	25	16	12	PA2	I/O	TTa	(4) (5)	USART2_TX, TIM2_CH3, TIM15_CH1, TSC_G1_IO3, COMP2_OUT, EVENTOUT	ADC1_IN3, COMP2_INM, OPAMP1_VOUT
G7	26	17	13	PA3	I/O	TTa	(4)	USART2_RX, TIM2_CH4, TIM15_CH2, TSC_G1_IO4, EVENTOUT	ADC1_IN4, OPAMP1_VINP, COMP2_INP, OPAMP1_VINM
-	27	18	-	PF4	I/O	TTa	(1) (4)	COMP1_OUT, EVENTOUT	ADC1_IN5
K9, K10	-	-	-	VSS	S	-	-	Digital ground	
K8	28	19	-	VDD	S	-	-	Digital power supply	
J7	29	20	14	PA4	I/O	TTa	(4) (5)	SPI1_NSS, SPI3_NSS, I2S3_WS, USART2_CK, TSC_G2_IO1, TIM3_CH2, EVENTOUT	ADC2_IN1, DAC1_OUT1, COMP1_INM, COMP2_INM, COMP4_INM, COMP6_INM
H7	30	21	15	PA5	I/O	TTa	(4) (5)	SPI1_SCK, TIM2_CH1_ETR, TSC_G2_IO2, EVENTOUT	ADC2_IN2 OPAMP1_VINP, OPAMP2_VINM COMP1_INM, COMP2_INM, COMP4_INM, COMP6_INM
H6	31	22	16	PA6	I/O	TTa	(4) (5)	SPI1_MISO, TIM3_CH1, TIM1_BKIN, TIM16_CH1, COMP1_OUT, TSC_G2_IO3, EVENTOUT	ADC2_IN3, OPAMP2_VOUT
K7	32	23	17	PA7	I/O	TTa	(4)	SPI1_MOSI, TIM3_CH2, TIM17_CH1, TIM1_CH1N, , TSC_G2_IO4, COMP2_OUT, EVENTOUT	ADC2_IN4, COMP2_INP, OPAMP2_VINP, OPAMP1_VINP
G6	33	24	-	PC4	I/O	TTa	(1) (4)	USART1_TX, EVENTOUT	ADC2_IN5
F6	34	25	-	PC5	I/O	TTa	(1)	USART1_RX, TSC_G3_IO1, EVENTOUT	ADC2_IN11, OPAMP2_VINM, OPAMP1_VINM
J6	35	26	18	PB0	I/O	TTa	-	TIM3_CH3, TIM1_CH2N, TSC_G3_IO2, EVENTOUT	COMP4_INP, OPAMP2_VINP

Table 13. STM32F302xB/STM32F302xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
E2	70	44	32	PA11	I/O	FT	-	USART1_CTS, USB_DM, CAN_RX, TIM1_CH1N, TIM1_CH4, TIM1_BKIN2, TIM4_CH1, COMP1_OUT, EVENTOUT	-
D1	71	45	33	PA12	I/O	FT	-	USART1_RTS_DE, USB_DP, CAN_TX, TIM1_CH2N, TIM1_ETR, TIM4_CH2, TIM16_CH1, COMP2_OUT, EVENTOUT	-
E3	72	46	34	PA13	I/O	FT	-	USART3_CTS, TIM4_CH3, TIM16_CH1N, TSC_G4_IO3, IR_OUT, SWDIO-JTMS, EVENTOUT	-
C1	73	-	-	PF6	I/O	FTf	(1)	I2C2_SCL, USART3_RTS_DE, TIM4_CH4, EVENTOUT	-
A1, A2, B1	74	47	35	VSS	S	-	-	Ground	
D2	75	48	36	VDD	S	-	-	Digital power supply	
C2	76	49	37	PA14	I/O	FTf	-	I2C1_SDA, USART2_TXTIM1_BKIN, TSC_G4_IO4, SWCLK-JTCK, EVENTOUT	-
B2	77	50	38	PA15	I/O	FTf	-	I2C1_SCL, SPI1_NSS, SPI3_NSS, I2S3_WS, JTDI, USART2_RX, TIM1_BKIN, TIM2_CH1_ETR, EVENTOUT	-
E4	78	51	-	PC10	I/O	FT	(1)	SPI3_SCK, I2S3_CK, USART3_TX, UART4_TX, EVENTOUT	-
D3	79	52	-	PC11	I/O	FT	(1)	SPI3_MISO, I2S3ext_SD, USART3_RX, UART4_RX, EVENTOUT	-
A3	80	53	-	PC12	I/O	FT	(1)	SPI3_MOSI, I2S3_SD, USART3_CK, UART5_TX, EVENTOUT	-
B3	81	-	-	PD0	I/O	FT	(1)	CAN_RX, EVENTOUT	-



Table 15. Alternate functions for port B (continued)

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF12	AF15
PB13	-	-	-	TSC_G6_IO3	-	SPI2_SCK, I2S2_CK	TIM1_CH1N	USART3_CTS	-	-	-	-	EVENT OUT
PB14	-	TIM15_CH1	-	TSC_G6_IO4	-	SPI2_MISO, I2S2ext_SD	TIM1_CH2N	USART3_RTS_DE	-	-	-	-	EVENT OUT
PB15	RTC_REFIN	TIM15_CH2	TIM15_CH1N	-	TIM1_CH3N	SPI2_MOSI, I2S2_SD	-	-	-	-	-	-	EVENT OUT

Table 18. Alternate functions for port E

Port & Pin Name	AF0	AF1	AF2	AF3	AF4	AF6	AF7
PE0	-	EVENTOUT	TIM4_ETR	-	TIM16_CH1	-	USART1_TX
PE1	-	EVENTOUT	-	-	TIM17_CH1	-	USART1_RX
PE2	TRACECK	EVENTOUT	TIM3_CH1	TSC_G7_IO1	-	-	-
PE3	TRACED0	EVENTOUT	TIM3_CH2	TSC_G7_IO2	-	-	-
PE4	TRACED1	EVENTOUT	TIM3_CH3	TSC_G7_IO3	-	-	-
PE5	TRACED2	EVENTOUT	TIM3_CH4	TSC_G7_IO4	-	-	-
PE6	TRACED3	EVENTOUT		-	-	-	-
PE7	-	EVENTOUT	TIM1_ETR	-	-	-	-
PE8	-	EVENTOUT	TIM1_CH1N	-	-	-	-
PE9	-	EVENTOUT	TIM1_CH1	-	-	-	-
PE10	-	EVENTOUT	TIM1_CH2N	-	-	-	-
PE11	-	EVENTOUT	TIM1_CH2	-	-	-	-
PE12	-	EVENTOUT	TIM1_CH3N	-	-	-	-
PE13	-	EVENTOUT	TIM1_CH3	-	-	-	-
PE14	-	EVENTOUT	TIM1_CH4	-	-	TIM1_BKIN2	-
PE15	-	EVENTOUT	TIM1_BKIN	-	-	-	USART3_RX

Table 19. Alternate functions for port F

Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PF0	-	-	-	I2C2_SDA	-	TIM1_CH3N	-
PF1	-	-	-	I2C2_SCL	-	-	-
PF2	EVENTOUT	-	-	-	-	-	-
PF4	EVENTOUT	COMP1_OUT	-	-	-	-	-
PF6	EVENTOUT	TIM4_CH4	-	I2C2_SCL	-	-	USART3_RTS_DE
PF9	EVENTOUT	-	TIM15_CH1	-	SPI2_SCK	-	-
PF10	EVENTOUT	-	TIM15_CH2	-	SPI2_SCK	-	-

Table 37. Switching output I/O current consumption

Symbol	Parameter	Conditions ⁽¹⁾	I/O toggling frequency (f _{SW})	Typ	Unit
I _{SW}	I/O current consumption	$V_{DD} = 3.3\text{ V}$ $C_{ext} = 0\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.90	mA
			4 MHz	0.93	
			8 MHz	1.16	
			18 MHz	1.60	
			36 MHz	2.51	
			48 MHz	2.97	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 10\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.93	
			4 MHz	1.06	
			8 MHz	1.47	
			18 MHz	2.26	
			36 MHz	3.39	
			48 MHz	5.99	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 22\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.03	
			4 MHz	1.30	
			8 MHz	1.79	
			18 MHz	3.01	
			36 MHz	5.99	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 33\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.10	
			4 MHz	1.31	
			8 MHz	2.06	
			18 MHz	3.47	
			36 MHz	8.35	
		$V_{DD} = 3.3\text{ V}$ $C_{ext} = 47\text{ pF}$ $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.20	
			4 MHz	1.54	
			8 MHz	2.46	
			18 MHz	4.51	
			36 MHz	9.98	

1. CS = 5 pF (estimated value).

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

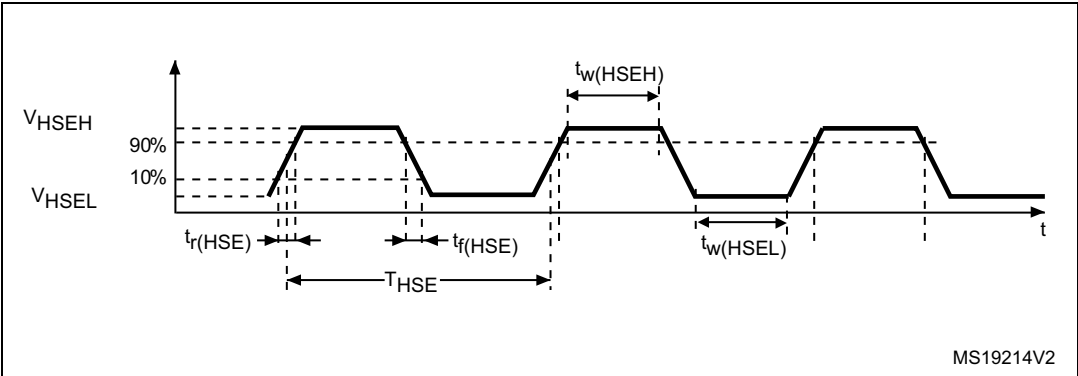
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO. The external clock signal has to respect the I/O characteristics in [Section 6.3.14](#). However, the recommended clock input waveform is shown in [Figure 14](#).

Table 40. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency ⁽¹⁾	-	1	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time ⁽¹⁾		15	-	-	ns
$t_r(HSE)$ $t_f(HSE)$	OSC_IN rise or fall time ⁽¹⁾		-	-	20	

1. Guaranteed by design.

Figure 14. High-speed external clock source AC timing diagram



MS19214V2

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in [Table 42](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 42. HSE oscillator characteristics

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Typ	Max ⁽²⁾	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	k Ω
I_{DD}	HSE current consumption	During startup ⁽³⁾	-	-	8.5	mA
		$V_{DD}=3.3\text{ V}$, $R_m=30\Omega$, $CL=10\text{ pF}@8\text{ MHz}$	-	0.4	-	
		$V_{DD}=3.3\text{ V}$, $R_m=45\Omega$, $CL=10\text{ pF}@8\text{ MHz}$	-	0.5	-	
		$V_{DD}=3.3\text{ V}$, $R_m=30\Omega$, $CL=5\text{ pF}@32\text{ MHz}$	-	0.8	-	
		$V_{DD}=3.3\text{ V}$, $R_m=30\Omega$, $CL=10\text{ pF}@32\text{ MHz}$	-	1	-	
		$V_{DD}=3.3\text{ V}$, $R_m=30\Omega$, $CL=20\text{ pF}@32\text{ MHz}$	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}^{(4)}$	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in [Table 43](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

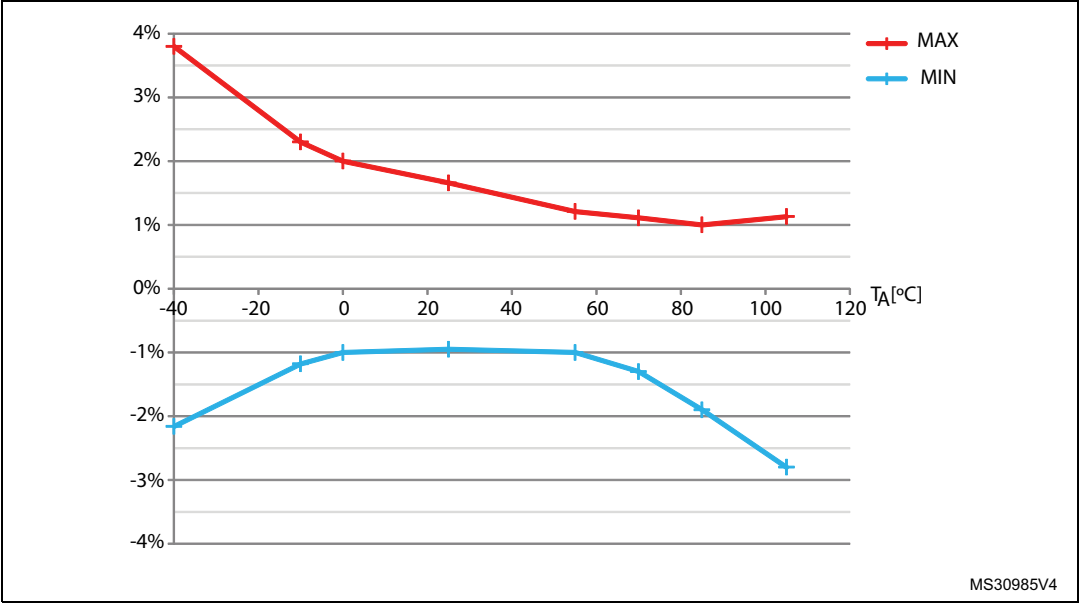
Table 43. LSE oscillator characteristics ($f_{LSE} = 32.768$ kHz)

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Typ	Max ⁽²⁾	Unit
I_{DD}	LSE current consumption	LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9	μA
		LSEDRV[1:0]=10 medium low driving capability	-	-	1	
		LSEDRV[1:0]=01 medium high driving capability	-	-	1.3	
		LSEDRV[1:0]=11 higher driving capability	-	-	1.6	
g_m	Oscillator transconductance	LSEDRV[1:0]=00 lower driving capability	5	-	-	$\mu A/V$
		LSEDRV[1:0]=10 medium low driving capability	8	-	-	
		LSEDRV[1:0]=01 medium high driving capability	15	-	-	
		LSEDRV[1:0]=11 higher driving capability	25	-	-	
$t_{SU(LSE)}^{(3)}$	Startup time	V_{DD} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
2. Guaranteed by design.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 18. HSI oscillator accuracy characterization results for soldered parts



Low-speed internal (LSI) RC oscillator

Table 45. LSI oscillator characteristics⁽¹⁾

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}^{(2)}$	LSI oscillator startup time	-	-	85	μs
$I_{DD(LSI)}^{(2)}$	LSI oscillator power consumption	-	0.75	1.2	μA

1. $V_{DDA} = 3.3 V$, $T_A = -40$ to $105^\circ C$ unless otherwise specified.
2. Guaranteed by design.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 50. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f _{HSE} /f _{HCLK}]	Unit
				8/72 MHz	
S _{EMI}	Peak level	V _{DD} = 3.6 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2	0.1 to 30 MHz	7	dBμV
			30 to 130 MHz	20	
			130 MHz to 1GHz	27	
			SAE EMI Level	4	-

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114, ANSI/ESD STM5.3.1 standard.

Table 51. ESD absolute maximum ratings

Symbol	Ratings	Conditions		Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to JESD22-A114		2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1	WLCSP100 package	3	250	
			Packages except WLCSP100	4	500	

1. Guaranteed by characterization results.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 22](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 22](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 55](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 24](#). All I/Os (FT, TTA and TC unless otherwise specified) are CMOS and TTL compliant.

Table 55. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	V
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OL}^{(1)}$	Output low level voltage for an I/O pin	TTL port ⁽²⁾ $I_{IO} = +8$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +20$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	1.3	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-1.3$	-	
$V_{OL}^{(1)(4)}$	Output low level voltage for an I/O pin	$I_{IO} = +6$ mA $2\text{ V} < V_{DD} < 2.7\text{ V}$	-	0.4	
$V_{OH}^{(3)(4)}$	Output high level voltage for an I/O pin		$V_{DD}-0.4$	-	
$V_{OLFM+}^{(1)(4)}$	Output low level voltage for an FTf I/O pin in FM+ mode	$I_{IO} = +20$ mA $2.7\text{ V} < V_{DD} < 3.6\text{ V}$	-	0.4	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 22](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 22](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed $\Sigma I_{IO(PIN)}$.
4. Data based on design simulation.

Table 59. IWDG min/max timeout period at 40 kHz (LSI) ⁽¹⁾

Prescaler divider	PR[2:0] bits	Min timeout (ms) RL[11:0]= 0x000	Max timeout (ms) RL[11:0]= 0xFFFF
/4	0	0.1	409.6
/8	1	0.2	819.2
/16	2	0.4	1638.4
/32	3	0.8	3276.8
/64	4	1.6	6553.6
/128	5	3.2	13107.2
/256	7	6.4	26214.4

1. These timings are given for a 40 kHz clock but the microcontroller's internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 60. WWDG min-max timeout value @72 MHz (PCLK)⁽¹⁾

Prescaler	WDGTB	Min timeout value	Max timeout value
1	0	0.05687	3.6409
2	1	0.1137	7.2817
4	2	0.2275	14.564
8	3	0.4551	29.127

1. Guaranteed by design.

Table 68. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{ADC}	ADC clock frequency	-	0.14	-	72	MHz
$f_{\text{S}}^{(1)}$	Sampling rate	Resolution = 12 bits, Fast Channel	0.01	-	5.14	MSPS
		Resolution = 10 bits, Fast Channel	0.012	-	6	
		Resolution = 8 bits, Fast Channel	0.014	-	7.2	
		Resolution = 6 bits, Fast Channel	0.0175	-	9	
$f_{\text{TRIG}}^{(1)}$	External trigger frequency	$f_{\text{ADC}} = 72 \text{ MHz}$ Resolution = 12 bits	-	-	5.14	MHz
		Resolution = 12 bits	-	-	14	$1/f_{\text{ADC}}$
V_{AIN}	Conversion voltage range ⁽²⁾	-	0	-	$V_{\text{REF+}}$	V
$R_{\text{AIN}}^{(1)}$	External input impedance	-	-	-	100	k Ω
$C_{\text{ADC}}^{(1)}$	Internal sample and hold capacitor	-	-	5	-	pF
$t_{\text{STAB}}^{(1)}$	Power-up time	-	1			conversion cycle
$t_{\text{CAL}}^{(1)}$	Calibration time	$f_{\text{ADC}} = 72 \text{ MHz}$	1.56			μs
		-	112			$1/f_{\text{ADC}}$
$t_{\text{latr}}^{(1)}$	Trigger conversion latency Regular and injected channels without conversion abort	CKMODE = 00	1.5	2	2.5	$1/f_{\text{ADC}}$
		CKMODE = 01	-	-	2	$1/f_{\text{ADC}}$
		CKMODE = 10	-	-	2.25	$1/f_{\text{ADC}}$
		CKMODE = 11	-	-	2.125	$1/f_{\text{ADC}}$
$t_{\text{latrinj}}^{(1)}$	Trigger conversion latency Injected channels aborting a regular conversion	CKMODE = 00	2.5	3	3.5	$1/f_{\text{ADC}}$
		CKMODE = 01	-	-	3	$1/f_{\text{ADC}}$
		CKMODE = 10	-	-	3.25	$1/f_{\text{ADC}}$
		CKMODE = 11	-	-	3.125	$1/f_{\text{ADC}}$